10/050,426

1	
IS&R	Туре
L1	L#
3	Hits
(("6458699") or ("6509239") or ("6159852")).PN.	Search Text
USPAT; US-PGPUB $\begin{vmatrix} 2004/04/11:04 \end{vmatrix}$	DBs
2004/04/30 11:04	Time Stamp
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2	
BRS	Туре
12	L #
45	Hits
selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit \$5) with (silane\$1 or disilane\$1 or chloro-silane\$1 or chloro-silane\$1 or (chloro adj silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiHsub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or "Si.sub.2 H.sub.6" or "Si.sub.2 H.sub.6" or "Si-sub.2 or "SiCl2H2" or "SiClsub.2H.sub.2" or "SiClsub.2H.sub.2" H.sub.2" or "SiClsub.2 H.sub.2" or "SiClsub.2 H.sub.2" or "SiClsub.2	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	DBs
2004/04/30	Time Stamp
	Comme nts
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- 5	4	· ·	
BRS	BRS	BRS	Туре
L5	L4	1.3	L #
2	0	1494	Hits
2 and 3	2 same 3	crystal\$7 with ((BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or (barium-strontium-titanate) or ((tantalum adj (oxide or dioxide or pentoxide or pentoxide or "Ta2O5" or "Ta2O5" or "Ta.sub.2O.sub.5" or "TaO2 or "TaO2" or "TaO.sub.2" or "Ta	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	DBs
2004/04/30 11:40	2004/04/30 11:40	2004/04/30	Time Stamp
			Comme nts
			Error Er Definit ro ion rs
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Туре	L#	Hits	Search Text	DBs	Time Stamp	Comme Definit ro	Error Er Definitro ion rs
				USPAT; US-PGPUB;			
6 RRS	9.1	35621	crystal\$7 near5		2004/04/30		<u> </u>
	5	17066	(dielectric or insulat\$5) DERWENT;		11:43		
				IBM_TDB			***************************************
				USPAT; US-PGPUB;			**************************************
7 DDC	7	>		EPO; JPO;	2004/04/30		>
/ DNS	L/		Z Sallie O	DERWENT;	11:43		
				IBM_TDB			
				USPAT; US-PGPUB;			
	7 0	ስ		EPO; JPO;	2004/04/30		>
8 BRS	Lo	C	z and o	DERWENT;	11:43		
				IBM_TDB			***************************************

9	
BRS	Туре
	L #
1745	Hits
(polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chloro-silane\$1 or chloro-silane\$1 or (chloro adj silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or Si2H6 or "Si2H6" or "Si2H6" or "Si.sub.2H.sub.6" or "SiC12H2 or "SiC12H2" or "SiC1.sub.2H.sub.2" or "SiC1.sub.2H.sub.2" or "SiC1.sub.2"	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	DBs
2004/04/30 15:38	Time Stamp
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	Type	L#	Hits	Search Text	DBs	Time Stamp	Comme Definit ro	Error Er Definitro ion rs
					USPAT; US-PGPUB;			
10	DDC	T 10				2004/04/30		>
10	DNJ	L10		5 Sallie 7	DERWENT;	11:46		
					IBM_TDB			
					USPAT; US-PGPUB;			
- .	DDC	-				2004/04/30		>
1	DNJ	114		o allu y	DERWENT;	11:47		
					IBM_TDB			···············

Type L# Hits Search Text DBS Stamp Comme Definition of Comme Defin		
Search Text BBS Time Comme Definition selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or Chemical adj vapor adj deposit\$5) or chemical-vapor-deposit \$5) same (silane\$1 or chloro-silane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or gichloro adj silane\$1 or gichloro adj silane\$	12	
# Hits Search Text DBs Time Comme Date of the comme (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or chloro-silane\$1 or chloro-silane\$1 or (chloro-silane\$1 or chloro-silane\$1 or "SiH.sub.4" or "SiH.4" or "SiH.4" or "SiH.4" or "SiH.4" or "SiH.4" or "SiCJH2" or "SiCJSH2 or "SiCJSH2 or "SiCJSH2 or "SiCJSH2 or "SiCJSH2" or "SiCJSH2 or "SiCJSH2"	BRS	Type
selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or PECVD or LPCVD or PECVD or chemical adj vapor adj deposit\$5) or chemical-vapor-deposit \$5) same (silane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or "SiH4" or "SiH4" or "SiH4" or Si2H6 or "Si.sub.2H.sub.6" or "Si.sub.2H.sub.6" or "Si.cub.2H.sub.6" or "SiClsub.2H.sub.6" or "SiClsub.2H.sub.2"	L12	L#
Text DBs Stamp Comme Definit Stamp in the roly\$1 corpoly\$1 corpected or poly\$1 or hemical cordeposit ane\$1 or lor lane\$1 or la	428	Hits
Stamp Comme Definit ion nts ion S-PGPUB; 2004/04/30 15:35	selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit \$5) same (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "Si;Hsub.4" or Si2H6 or "Si;Sub.2H.sub.6" or "Si;Sub.2H.sub.6" or "Si;Cl2H2 or "SiCl2H2" or "SiClsub.2H.sub.2" or "SiClsub.2" or "SiClsub.2" H.sub.2" or "SiClsub.2" Cl.sub.2" or "SiClsub.2"	Search Text
comme Definit nts ion	3-PGPUB;	DBs
Definit	2004/04/30	Time Stamp
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USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
(crystal\$7 or mono-crystal\$7) or (mono adj crystal\$7)) with ((BST or "BST" or (barium adj strontium-titan adj titanate) or (barium-strontium-titan ate) or (tantalum adj or ((tantalum adj or ((tantalum adj pent-oxide or pentoxide or "Ta2O5" or "Ta2O5" or "Ta2O5" or "TaO2 or "TaO2" or "TaO.sub.2" or "TaO or "TaO.sub.2" or TaO or "TaO.sub.2" or TaO.sub.2" or TaO.sub.

	Type	L#	Hits	Search Text	DBs	Time Stamp	Comme Error Ernts Definitro	Error Er Definit ro ion rs
					USPAT; US-PGPUB;			
			1	10 110	EPO; JPO;	2004/04/30		
15	BKD	CIT		12 and 13	DERWENT;	13:59		
					IBM_TDB			
				(crystal\$7 or				
				mono-crystal\$7 or	USPAT; US-PGPUB;			
		T 16	126162	(mono adj crystal\$7))	EPO; JPO;	2004/04/30		
10	DNJ	017	70102	with (dielectric or	DERWENT;	14:02	***************************************	
				insulat\$4 or oxide or	IBM_TDB			
				dioxide or nitride)				
				-	USPAT; US-PGPUB;			
		1 17	7	10 22	EPO; JPO;	2004/04/30	·····	
1/	DNO	L1/ 21	17	12 Salile 10	DERWENT;	14:02	***************************************	
					IBM_TDB		·····	

	·-···
18	·
BRS	Туре
L18	L#
16	Hits
selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit \$5) same (silane\$1 or chloro-silane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or (chloro adj silane\$1) or (siH.sub.4" or "SiH4" or "SiH.sub.4" or Si2H6 or "Si.sub.2H.sub.6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or "SiC12H2 or "SiC12H2" or "SiC1.sub.2" or "Si C1.sub.2 H.sub.2" or "SiC1.sub.2 H.sub.2" or "SiC1.sub.2 H.sub.2" or top or second) ngar2 (plate\$1 version:	Search Text
US-PGPUB; O; OB DB	DBs
2004/04/30	Time Stamp
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	23 BRS	22 BRS	21 BRS	20 BRS	19 BRS	Туре
L24	L23	L22	L21	L20	L19	L#
158	16	29	0	16	545331	Hits
12 and 19	12 same 19	2 not 20	20 NOT 2	2 and 19	(upper or top or second) near2 (plate\$1 or electrode\$1)	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT;	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; · IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	DBs
2004/04/30 15:03	2004/04/30 14:58	2004/04/30 14:31	2004/04/30 14:30	2004/04/30 14:30	2004/04/30 14:25	Time Stamp
						Comme Defin
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Type L# Hits Search Text DBs Time Stamp Commed Definit room of Error Error Error Error Error Polysilicon or polysilicon o	29	28	27	26	25	
# Hits Search Text DBs Stamp Comme (polysilicon or poly\$1 EPO; JPO; JPO; or deposit\$5) USPAT; US-PGPUB; 2004/04/30 DERWENT; 2004	BRS	BRS	BRS	BRS	BRS	Туре
### Rits Search Text DBs Time (Comme (polysilicon or poly\$1 EPO; JPO; or (polycrystalline adj silicon)) with (form\$4 BM_TDB EPO; JPO; or deposit\$5) USPAT; US-PGPUB; 2004/04/30 15:36 IBM_TDB 15:36 IBM_TDB 2004/04/30 IBM_TDB 2004/04/30 IBM_TDB IS:37 IBM_TDB IS:37 IBM_TDB IS:40 IBM_TDB IS:41 IBM_TDB IBM_TDB IS:41 IBM_TDB IBM_	L29	L28	L27	L26	L25	L#
USPAT; US-PGPUB; 2004/04/30 DERWENT; IS:36 IS:36 IS:36 IS:36 IS:36 IS:37 IS:40 IS:41	27	71	44	223	10117	Hits
S-PGPUB; 2004/04/30 Γ; 15:36 S-PGPUB; 2004/04/30 Γ; 15:37 S-PGPUB; 2004/04/30 Γ; 15:40 S-PGPUB; 2004/04/30 Γ; 15:40 S-PGPUB; 2004/04/30 Γ; 15:40 I 15:40 I 15:40	28 NOT 27	9 same 25	9 with 25	25 and 12	selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (form\$4 or deposit\$5)	Search Text
ne Comme nts)4/30)4/30)4/30)4/30)4/30		J. S.	S.	Ţ.	T;	DBs
Comme Definit ranks ion ra	2004/04/30 15:41	2004/04/30 15:40	2004/04/30 15:40	2004/04/30 15:37	2004/04/30 15:36	Time Stamp
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0			2004/04/30 16:27	USPAT; US-PGPUB	30 or 31	21	L32	BRS	32
0			2004/04/30 16:27	USPAT; US-PGPUB	(("6013575") or ("4948755") or ("4966868") or ("5607878") or ("5663098") or ("6017823") or ("6069036") or ("5798278") or ("5798278") or ("5118639")).PN.	10	L31	IS&R	31
0			2004/04/30 16:25	USPAT; US-PGPUB	(("4497683") or ("4963506") or ("5080933") or ("5110757") or ("5124276") or ("5364815") or ("5441012") or ("5006911") or ("5818100") or ("58187775") or ("5646073")).PN.	二	L30	IS&R	30
Error Er Definit ro ion rs	ne	Comr nts	Time Stamp	DBs	Search Text	Hits	L#	Туре	

L Number	Hits	Search Text	DB	Time stamp
1	3	(("6458699") or ("6509239") or ("6159852")).PN.	USPAT;	2004/04/30 11:04
_			US-PGPUB	}
2	45	selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon))	USPAT,	2004/04/30 13:56
		with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj	US-PGPUB;	
		deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or	ЕРО; ЈРО;	
1		chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or	DERWENT;	
		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or	IBM_TDB	
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "SiCl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
		or "Si Cl.sub.2H.sub.2")		
3	1494	crystal\$7 with ((BST or "BST" or (barium adj strontium adj titanate) or	USPAT;	2004/04/30 13:57
1	1474	(barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum	US-PGPUB;	2004/04/30 13.5/
		adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5"	EPO; JPO;	
ľ		or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or	DERWENT;	
		"TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO"))	IBM_TDB	
4	0	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon))	USPAT;	2004/04/30 11:40
		with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj	US-PGPUB;	
		deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or	ЕРО; ЛРО;	
		chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or	DERWENT;	
		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or	IBM_TDB	
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or		
		"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
		or "Si Cl.sub.2H.sub.2")) same (crystal\$7 with ((BST or "BST" or		
		(barium adj strontium adj titanate) or (barium-strontium-titanate) or		
		bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or		
ļ		pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2"		
1		or TaO or "TaO")))		
5	2	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon))	USPAT;	2004/04/30 11:40
·	2	with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj	US-PGPUB;	2004/04/30 11:40
1		deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1-or	ЕРО; ЛРО;	
		chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or	DERWENT;	
-		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or	IBM TDB	
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or	_	
į		"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
		or "Si Cl.sub.2H.sub.2")) and (crystal\$7 with ((BST or "BST" or		
		(barium adj strontium adj titanate) or (barium-strontium-titanate) or		
		bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or		
		pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or		
		"Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2"		
_	35621	or TaO or "TaO"))) crystal\$7 near5 (dielectric or insulat\$5)	IICDAT.	2004/04/30 11:43
6	33021	crystals / flears (diefectife of flistiates)	USPAT; US-PGPUB;	2004/04/30 11.43
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
7	0	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon))	USPAT;	2004/04/30 11:43
	-	with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj	US-PGPUB;	
		deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or	ЕРО; ЛРО;	
		chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or	DERWENT;	
		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or	IBM_TDB	
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or		<u> </u>
1		"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
		an US: (1) and OII and OIN and (i	
		or "Si Cl.sub.2H.sub.2")) same (crystal\$7 near5 (dielectric or		
	ا ہ	insulat\$5))	1100	0004/04/00 10 10
8	5	insulat\$5)) (selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon))	USPAT;	2004/04/30 11:43
8	5	insulat\$5)) (selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj	US-PGPUB;	2004/04/30 11:43
8	5	insulat\$5)) (selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or	US-PGPUB; EPO; JPO;	2004/04/30 11:43
8	5	insulat\$5)) (selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or	US-PGPUB; EPO; JPO; DERWENT;	2004/04/30 11:43
8	5	insulat\$5)) (selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or	US-PGPUB; EPO; JPO;	2004/04/30 11:43
8	5	insulat\$5)) (selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or	US-PGPUB; EPO; JPO; DERWENT;	2004/04/30 11:43

9	1745	(polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or	USPAT;	2004/04/30 15:38
		PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or	US-PGPUB;	
		chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or	EPO; JPO;	
	[chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or	DERWENT;	
		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or	IBM_TDB	
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "SiCl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
10		or "Si Cl.sub.2H.sub.2") (crystal\$7 with ((BST or "BST" or (barium adj strontium adj titanate) or	USPAT;	2004/04/30 11:46
10	0		US-PGPUB;	2004/04/30 11.40
		(barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5"	ЕРО; ЛРО;	
		or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or	DERWENT;	
		"TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO"))) same ((polysilicon or	IBM_TDB	
		poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD	IDM_1DD	
		or APCVD or (chemical adj vapor adj deposit\$5) or		
		chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or	ĺ	
]	chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or		
	}	"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or		
	1	"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or		
	ļ ;	"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"	,	
		or "Si Cl.sub.2H.sub.2"))		
11	14	(crystal\$7 with ((BST or "BST" or (barium adj strontium adj titanate) or	USPAT;	2004/04/30 11:47
••	''	(barium-strontium-titanate) or bariumstrontium titanate) or ((tantalum	US-PGPUB;	
		adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5"	ЕРО; ЛРО;	
	1	or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or	DERWENT;	
		"TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO"))) and ((polysilicon or	IBM TDB	
		poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD		
		or APCVD or (chemical adj vapor adj deposit\$5) or		
		chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or		
		chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or		
		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or		
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or		
-		"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
		or "Si Cl.sub.2H.sub.2"))		
12	428	selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon))	USPAT;	2004/04/30 15:35
	1	same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor	US-PGPUB;	
		adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or	ЕРО; ЈРО;	
		disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1)	DERWENT;	
		or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6"	IBM_TDB	
	•	or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or		
		"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
12	1404	or "Si Cl.sub.2H.sub.2")	USPAT;	2004/04/30 14:01
13	1494	(crystal\$7 or mono-crystal\$7 or (mono adj crystal\$7)) with ((BST or "BST" or (barium adj strontium adj titanate) or	US-PGPUB;	2004/04/30 14.01
		(barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum	EPO; JPO;	
		adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5"	DERWENT;	
		or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or	IBM TDB	
		"TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO"))	IDIVI_IDD	
14	0	(selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon))	USPAT;	2004/04/30 13:58
• •	"	same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor	US-PGPUB;	
		adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or	ЕРО; ЈРО;	
		disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1)	DERWENT;	
		or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6"	IBM_TDB	
		or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or		
		"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
1	1	or "Si Cl.sub.2H.sub.2")) same ((crystal\$7 or mono-crystal\$7 or (mono		
		adj crystal\$7)) with ((BST or "BST" or (barium adj strontium adj]	
		titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate) or	1	
		((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5		
		or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or		
		"TaO2" or "TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO")))		

	· –			**************************************
15	7	(selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or disilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2") and ((crystal\$7 or mono-crystal\$7 or (mono adj crystal\$7)) with ((BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO")))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 13:59
16	136162	(crystal\$7 or mono-crystal\$7 or (mono adj crystal\$7)) with (dielectric or insulat\$4 or oxide or dioxide or nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:02
17	21	(selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2") same ((crystal\$7 or mono-crystal\$7 or (mono adj crystal\$7)) with (dielectric or insulat\$4 or oxide or dioxide or nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:02
18	16	selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or disilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2") same ((upper or top or second) near2 (plate\$1 or electrode\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:25
19	545331	(upper or top or second) near2 (plate\$1 or electrode\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/30 14:25
20	16	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2")) and ((upper or top or second) near2 (plate\$1 or electrode\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:30

	·			- 2
21	0	((selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:30
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "SiCl.sub.2 H.sub.2" or "SiCl.sub.2H.sub.2") and ((upper or top or second) near2 (plate\$1 or electrode\$1))) NOT (selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or		
		chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2"))		
22	29	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH4.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:31
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2") not ((selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or Chlorosilan		
		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2") and ((upper or top or second) near2 (plate\$1 or electrode\$1)))		·
23	16	(selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:58
24	158	or electrode\$1)) (selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) and ((upper or top or second) near2 (plate\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 15:03
25	10117	or electrode\$1)) selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (form\$4 or deposit\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 15:36

T26	222	(1 4 4 0 0 0 14 (1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	LICDATE	0004/04/20 15:27
26	223	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (form\$4 or deposit\$5)) and (selective\$3 same (polysilicon or	USPAT; US-PGPUB;	2004/04/30 15:37
		poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or	ЕРО; ЛРО;	
		LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or	DERWENT;	
		chemical-vapor-deposit\$5) same (silane\$1 or disilane\$1 or	IBM TDB	
		chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or	IDIVI_IDD	
		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or		
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or		
		"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
		or "Si Cl.sub.2H.sub.2"))		
27	44	((polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or	USPAT;	2004/04/30 15:40
		PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or	US-PGPUB;	
		chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or	ЕРО; ЛРО;	
		chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or	DERWENT;	
		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or	IBM_TDB	
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or	_	
		"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
		or "Si Cl.sub.2H.sub.2")) with (selective\$3 with (polysilicon or poly\$1		
		or (polycrystalline adj silicon)) with (form\$4 or deposit\$5))		
28	71	((polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or	USPAT;	2004/04/30 15:40
		PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or	US-PGPUB;	
	,	chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or	ЕРО; ЈРО;	
		chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or	DERWENT;	
		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or	IBM_TDB	
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or		
		"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
		or "Si Cl.sub.2H.sub.2")) same (selective\$3 with (polysilicon or poly\$1		
		or (polycrystalline adj silicon)) with (form\$4 or deposit\$5))		
29	27	(((polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or	USPAT;	2004/04/30 15:41
		PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or	US-PGPUB;	
		chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or	ЕРО; ЈРО;	
		chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or	DERWENT;	
1		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or	IBM_TDB	
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or	:	
	!	"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
		or "Si Cl.sub.2H.sub.2")) same (selective\$3 with (polysilicon or poly\$1		
]	or (polycrystalline adj silicon)) with (form\$4 or deposit\$5))) NOT		
	ļ	(((polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or		
1	ļ	PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or		
		chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or		
		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or		
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or		
		"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
		or "Si Cl.sub.2H.sub.2")) with (selective\$3 with (polysilicon or poly\$1		
		or (polycrystalline adj silicon)) with (form\$4 or deposit\$5)))		
30	11	(("4497683") or ("4963506") or ("5080933") or ("5110757") or	USPAT;	2004/04/30 16:25
"	'''	("5124276") or ("5364815") or ("5441012") or ("5006911") or	US-PGPUB	
		("5818100") or ("5037775") or ("5646073")).PN.		
31	10	(("6013575") or ("4948755") or ("4966868") or ("5607878") or	USPAT;	2004/04/30 16:27
		("5663098") or ("6017823") or ("6069036") or ("5798278") or	US-PGPUB	
		("5037778") or ("5118639")).PN.		
32	21	((("4497683") or ("4963506") or ("5080933") or ("5110757") or	USPAT;	2004/04/30 16:27
		("5124276") or ("5364815") or ("5441012") or ("5006911") or	US-PGPUB	
		("5818100") or ("5037775") or ("5646073")).PN.) or ((("6013575") or		
		("4948755") or ("4966868") or ("5607878") or ("5663098") or		
		("6017823") or ("6069036") or ("5798278") or ("5037778") or		
		("5118639")).PN.)	!	
-	3		USPAT;	2003/07/13 12:00
		· ·	US-PGPUB	

-	431	selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5)) with (silicon or silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or "SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 11:38
-	465444	(upper or second or top or another) adj3 (plate\$1 or electrode\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/13 11:40
-	11	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5)) with (silicon or silane\$1 or disilane\$1 or chlorosilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si sub.2 H.sub.6" or "SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2") with ((upper or second or top or another) adj3 (plate\$1 or electrode\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/13 11:40
-	3	(("4497683") or ("5006911") or ("4963506")).PN.	USPAT; US-PGPUB	2003/07/13 12:02
-	25	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5)) with (silicon or silane\$1 or disilane\$1 or chlorosilane\$1 or chlorosilane\$1 or chlorosilane\$1 or chlorosilane\$1 or chlorosilane\$1 or "SiH4" or "SiH.sub.4" or "Si2H6" or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or "SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2")) same ((upper or second or top or another) adj3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/13 12:11
		(plate\$1 or electrode\$1))	Tran . m	2002/07/12 12 12
-	581471	capacitor or capacitors or DRAM or DRAMs	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/13 12:12
-	5953	BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/13 12:14
-	26351	(tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/13 12:19
-	1480	(capacitor or capacitors or DRAM or DRAMs) and (BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate) and ((tantalum adj (oxide or dioxide or pentoxide or pentoxide or pentoxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2O.sub.5" or "TaO.sub.2" or "TaO.sub.2"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/13 12:43
-	1289	or TaO or "TaO") crystal\$7 with ((BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 11:39

-	615	(capacitor or capacitors or DRAM or DRAMs) and (crystal\$7 with	USPAT;	2003/07/13 12:44
		((BST or "BST" or (barium adj strontium adj titanate) or	US-PGPUB;	
		(barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum	ЕРО; ЈРО;	
		adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5"	DERWENT;	
1		or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or	IBM_TDB	
		"TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO")))		
-	788		USPAT;	2003/07/13 12:45
		with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj	US-PGPUB;	
		deposit\$5))	ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
-	9	((capacitor or capacitors or DRAM or DRAMs) and (crystal\$7 with	USPAT;	2003/07/13 12:47
		((BST or "BST" or (barium adj strontium adj titanate) or	US-PGPUB;	
		(barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum	ЕРО; ЛРО;	
		adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5"	DERWENT;	
		or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or	IBM_TDB	
	j	"TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO")))) and (selective\$3 with		
		(polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or	ļ	
		PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5))	!	
		with (silicon or silane\$1 or disilane\$1 or chlorosilane\$1 or		
		chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or		
		"SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or "SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2"		
		or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si		
		C1.sub.2H.sub.2"))	<u> </u>	L